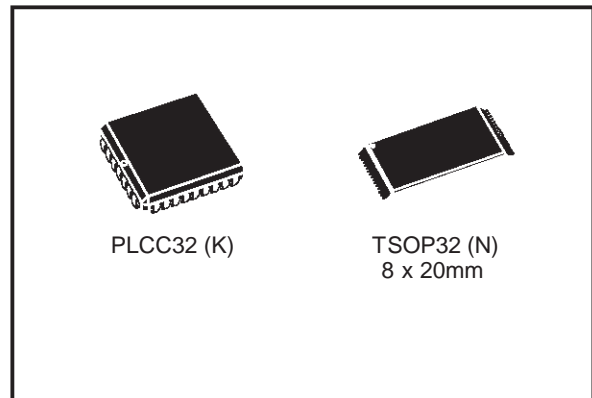


8 Mbit (1Mb x 8) Low Voltage OTP EPROM

- **LOW VOLTAGE READ OPERATION:**
2.7V to 3.6V
- **FAST ACCESS TIME:**
 - 70ns at $V_{CC} = 3.0V$ to 3.6V
 - 80ns at $V_{CC} = 2.7V$ to 3.6V
- **LOW POWER CONSUMPTION:**
 - Active Current 15mA
 - Standby Current 20 μ A
- **PROGRAMMING VOLTAGE:** 12.75V \pm 0.25V
- **PROGRAMMING TIMES** of AROUND 52sec. (PRESTO IIB ALGORITHM)
- **ELECTRONIC SIGNATURE**
 - Manufacturer Code: 20h
 - Device Code: 42h



DESCRIPTION

The M27W801 is a low voltage 8 Mbit EPROM offered in the OTP ranges (one time programmable). It is ideally suited for microprocessor systems requiring large data or program storage and is organized as 1,048,576 by 8 bits.

The M27W801 operates in the read mode with a supply voltage as low as 2.7V at -40 to $85^{\circ}C$ temperature range. The decrease in operating power allows either a reduction of the size of the battery or an increase in the time between battery recharges.

The M27W801 is offered in PLCC32 and TSOP32 (8 x 20 mm) packages.

Figure 1. Logic Diagram

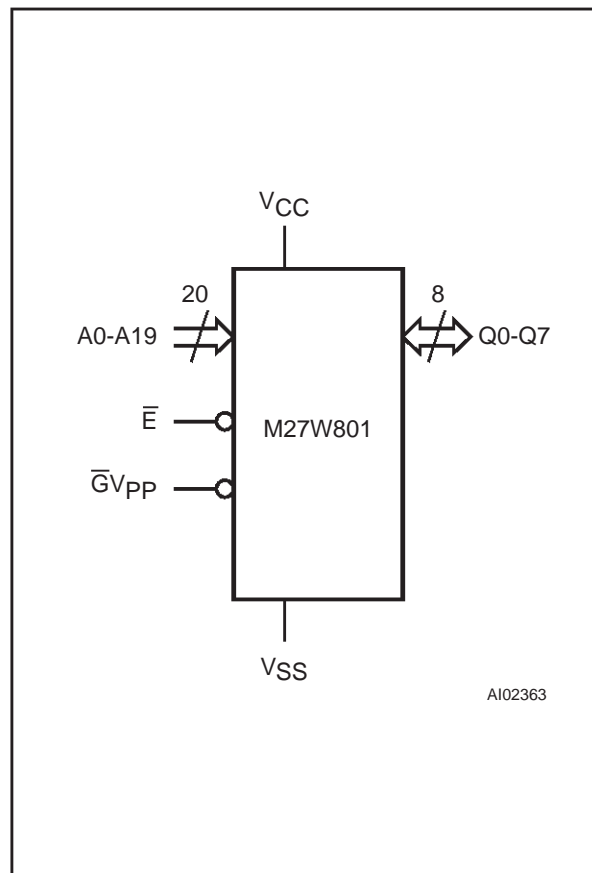


Table 1. Signal Names

A0-A19	Address Inputs
Q0-Q7	Data Outputs
\bar{E}	Chip Enable
$\bar{G}V_{PP}$	Output Enable / Program Supply
V_{CC}	Supply Voltage
V_{SS}	Ground

Figure 2A. PLCC Pin Connections

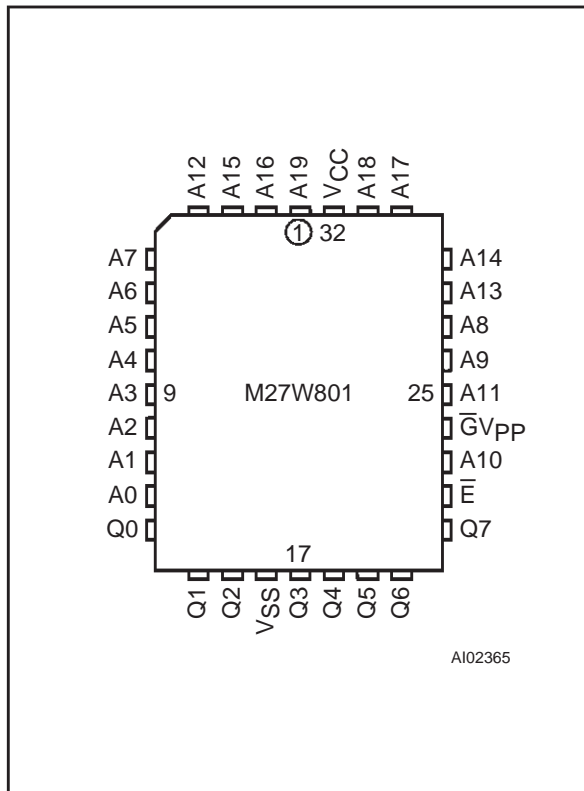


Figure 2B. TSOP Pin Connections

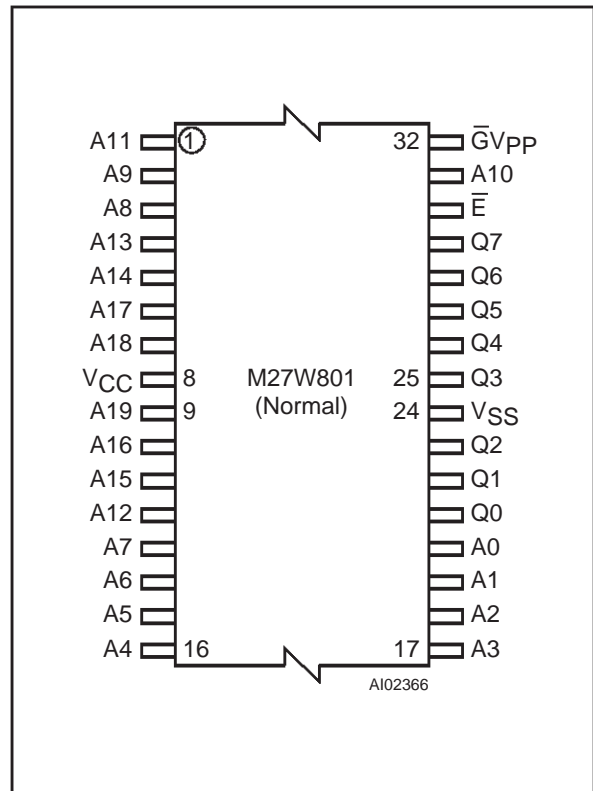


Table 2. Absolute Maximum Ratings ⁽¹⁾

Symbol	Parameter	Value	Unit
T _A	Ambient Operating Temperature ⁽³⁾	-40 to 85	°C
T _{BIAS}	Temperature Under Bias	-50 to 125	°C
T _{STG}	Storage Temperature	-65 to 150	°C
V _{IO} ⁽²⁾	Input or Output Voltages (except A9)	-2 to 7	V
V _{CC}	Supply Voltage	-2 to 7	V
V _{A9} ⁽²⁾	A9 Voltage	-2 to 13.5	V
V _{PP}	Program Supply Voltage	-2 to 14	V

Notes: 1. Except for the rating "Operating Temperature Range", stresses above those listed in the Table "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the Operating sections of this specification is not implied. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability. Refer also to the SGS-THOMSON SURE Program and other relevant quality documents.

2. Minimum DC voltage on Input or Output is -0.5V with possible undershoot to -2.0V for a period less than 20ns. Maximum DC voltage on Output is V_{CC} +0.5V with possible overshoot to V_{CC} +2V for a period less than 20ns.

3. Depends on range.

Table 3. Operating Modes

Mode	\bar{E}	$\bar{G}V_{PP}$	A9	Q0 - Q7
Read	V_{IL}	V_{IL}	X	Data Out
Output Disable	V_{IL}	V_{IH}	X	Hi-Z
Program	V_{IL} Pulse	V_{PP}	X	Data In
Program Inhibit	V_{IH}	V_{PP}	X	Hi-Z
Standby	V_{IH}	X	X	Hi-Z
Electronic Signature	V_{IL}	V_{IL}	V_{ID}	Codes

Note: X = V_{IH} or V_{IL} , $V_{ID} = 12V \pm 0.5V$.

Table 4. Electronic Signature

Identifier	A0	Q7	Q6	Q5	Q4	Q3	Q2	Q1	Q0	Hex Data
Manufacturer's Code	V_{IL}	0	0	1	0	0	0	0	0	20h
Device Code	V_{IH}	0	1	0	0	0	0	1	0	42h

DEVICE OPERATION

The operating modes of the M27W801 are listed in the Operating Modes table. A single power supply is required in the read mode. All inputs are TTL levels except for $\bar{G}V_{PP}$ and 12V on A9 for Electronic Signature and Margin Mode Set or Reset.

Read Mode

The M27W801 has two control functions, both of which must be logically active in order to obtain data at the outputs. Chip Enable (\bar{E}) is the power control and should be used for device selection. Output Enable (\bar{G}) is the output control and should be used to gate data to the output pins, independent of device selection. Assuming that the addresses are stable, the address access time (t_{AVQV}) is equal to the delay from \bar{E} to output (t_{ELQV}). Data is available at the output after a delay of t_{GLQV} from the falling edge of \bar{G} , assuming that \bar{E} has been low and the addresses have been stable for at least $t_{AVQV} - t_{GLQV}$.

Standby Mode

The M27W801 has a standby mode which reduces the supply current from 15mA to 20 μ A with low voltage operation $V_{CC} \leq 3.6V$, see Read Mode DC

Characteristics table for details. The M27W801 is placed in the standby mode by applying a CMOS high signal to the \bar{E} input. When in the standby mode, the outputs are in a high impedance state, independent of the $\bar{G}V_{PP}$ input.

Two Line Output Control

Because EPROMs are usually used in larger memory arrays, the product features a 2 line control function which accommodates the use of multiple memory connection. The two line control function allows:

- the lowest possible memory power dissipation,
- complete assurance that output bus contention will not occur.

For the most efficient use of these two control lines, \bar{E} should be decoded and used as the primary device selecting function, while \bar{G} should be made a common connection to all devices in the array and connected to the \overline{READ} line from the system control bus. This ensures that all deselected memory devices are in their low power standby mode and that the output pins are only active when data is required from a particular memory device.

Table 5. AC Measurement Conditions

	High Speed	Standard
Input Rise and Fall Times	≤ 10ns	≤ 20ns (10% to 90%)
Input Pulse Voltages	0 to 3V	0.4V to 2.4V
Input and Output Timing Ref. Voltages	1.5V	0.8V and 2V

Figure 3. AC Testing Input Output Waveform

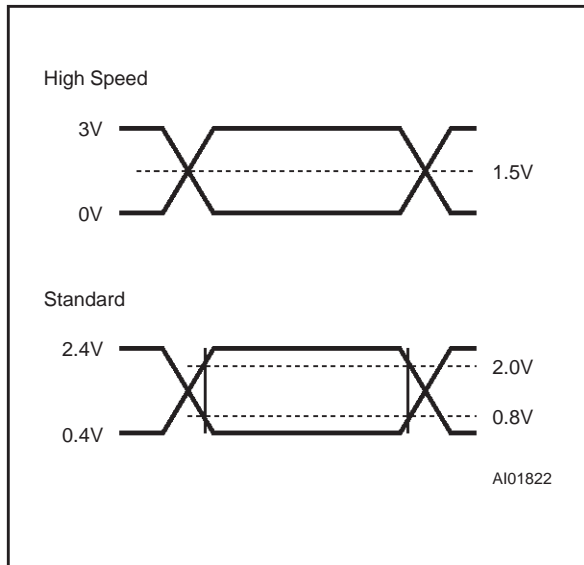


Figure 4. AC Testing Load Circuit

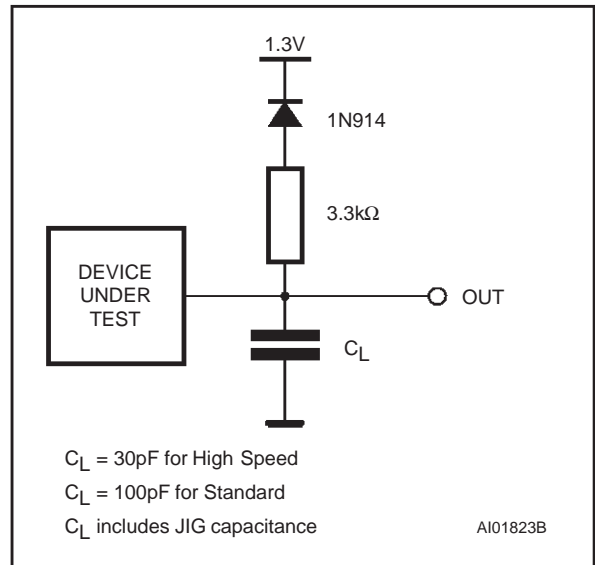


Table 6. Capacitance⁽¹⁾ (T_A = 25 °C, f = 1 MHz)

Symbol	Parameter	Test Condition	Min	Max	Unit
C _{IN}	Input Capacitance	V _{IN} = 0V		6	pF
C _{OUT}	Output Capacitance	V _{OUT} = 0V		12	pF

Note: 1. Sampled only, not 100% tested.

System Considerations

The power switching characteristics of Advanced CMOS EPROMs require careful decoupling of the devices. The supply current, I_{CC}, has three segments that are of interest to the system designer: the standby current level, the active current level, and transient current peaks that are produced by the falling and rising edges of \bar{E} . The magnitude of the transient current peaks is dependent on the capacitive and inductive loading of the device at the output.

The associated transient voltage peaks can be suppressed by complying with the two line output

control and by properly selected decoupling capacitors. It is recommended that a 0.1μF ceramic capacitor be used on every device between V_{CC} and V_{SS}. This should be a high frequency capacitor of low inherent inductance and should be placed as close to the device as possible. In addition, a 4.7μF bulk electrolytic capacitor should be used between V_{CC} and V_{SS} for every eight devices. The bulk capacitor should be located near the power supply connection point. The purpose of the bulk capacitor is to overcome the voltage drop caused by the inductive effects of PCB traces.

Table 7. Read Mode DC Characteristics (1)(T_A = -40 to 85 °C; V_{CC} = 2.7V to 3.6V; V_{PP} = V_{CC})

Symbol	Parameter	Test Condition	Min	Max	Unit
I _{LI}	Input Leakage Current	0V ≤ V _{IN} ≤ V _{CC}		±10	μA
I _{LO}	Output Leakage Current	0V ≤ V _{OUT} ≤ V _{CC}		±10	μA
I _{CC}	Supply Current	$\bar{E} = V_{IL}, \bar{G}V_{PP} = V_{IL},$ I _{OUT} = 0mA, f = 5MHz V _{CC} ≤ 3.6V		15	mA
I _{CC1}	Supply Current (Standby) TTL	$\bar{E} = V_{IH}$		1	mA
I _{CC2}	Supply Current (Standby) CMOS	$\bar{E} > V_{CC} - 0.2V$ V _{CC} ≤ 3.6V		20	μA
I _{PP}	Program Current	V _{PP} = V _{CC}		10	μA
V _{IL}	Input Low Voltage		-0.6	0.2 V _{CC}	V
V _{IH} (2)	Input High Voltage		0.7 V _{CC}	V _{CC} + 0.5	V
V _{OL}	Output Low Voltage	I _{OL} = 2.1mA		0.4	V
V _{OH}	Output High Voltage TTL	I _{OH} = -1mA	3.6		V

Notes: 1. V_{CC} must be applied simultaneously with or before V_{PP} and removed simultaneously or after V_{PP}.
2. Maximum DC voltage on Output is V_{CC} + 0.5V.

Table 8. Read Mode AC Characteristics (1)(T_A = -40 to 85 °C; V_{CC} = 2.7V to 3.6V; V_{PP} = V_{CC})

Symbol	Alt	Parameter	Test Condition	M27W801						Unit
				-80 (3)				-100 (-120/-150/-200)		
				V _{CC} = 3.0V to 3.6V		V _{CC} = 2.7V to 3.6V		V _{CC} = 2.7V to 3.6V		
				Min	Max	Min	Max	Min	Max	
t _{AVQV}	t _{ACC}	Address Valid to Output Valid	$\bar{E} = V_{IL},$ $\bar{G} = V_{IL}$		70		80		100	ns
t _{ELQV}	t _{CE}	Chip Enable Low to Output Valid	$\bar{G} = V_{IL}$		70		80		100	ns
t _{GLQV}	t _{OE}	Output Enable Low to Output Valid	$\bar{E} = V_{IL}$		40		50		60	ns
t _{EHQZ} (2)	t _{DF}	Chip Enable High to Output Hi-Z	$\bar{G} = V_{IL}$	0	50	0	50	0	60	ns
t _{GHQZ} (2)	t _{DF}	Output Enable High to Output Hi-Z	$\bar{E} = V_{IL}$	0	50	0	50	0	60	ns
t _{AXQX}	t _{OH}	Address Transition to Output Transition	$\bar{E} = V_{IL},$ $\bar{G} = V_{IL}$	0		0		0		ns

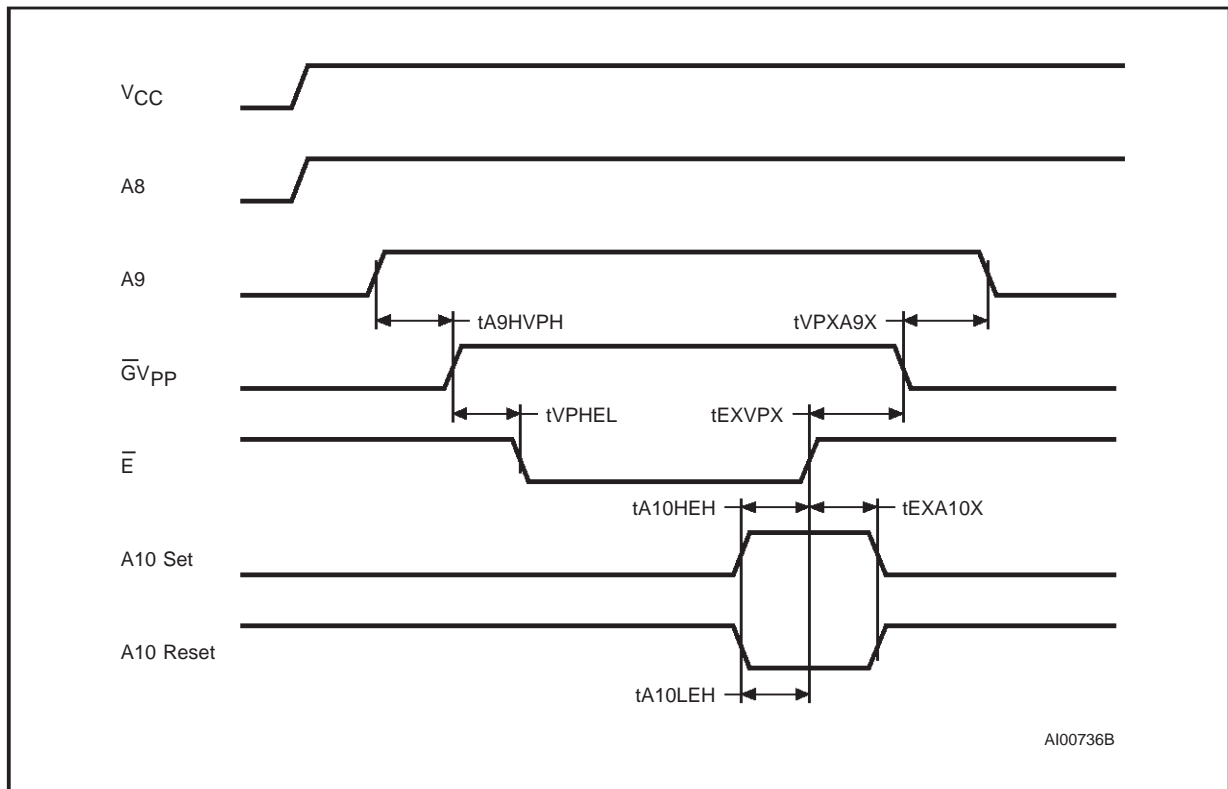
Notes: 1. V_{CC} must be applied simultaneously with or before V_{PP} and removed simultaneously or after V_{PP}.
2. Sampled only, not 100% tested.
3. Speed obtained with High Speed AC measurement conditions.

Table 10. MARGIN MODE AC Characteristics (1)
 ($T_A = 25\text{ }^\circ\text{C}$; $V_{CC} = 6.25\text{V} \pm 0.25\text{V}$; $V_{PP} = 12.75\text{V} \pm 0.25\text{V}$)

Symbol	Alt	Parameter	Test Condition	Min	Max	Unit
t_{A9HVPH}	t_{AS9}	VA9 High to V_{PP} High		2		μs
t_{VPHEL}	t_{VPS}	V_{PP} High to Chip Enable Low		2		μs
t_{A10HEH}	t_{AS10}	VA10 High to Chip Enable High (Set)		1		μs
t_{A10LEH}	t_{AS10}	VA10 Low to Chip Enable High (Reset)		1		μs
t_{EXA10X}	t_{AH10}	Chip Enable Transition to VA10 Transition		1		μs
t_{EXVPX}	t_{VPH}	Chip Enable Transition to V_{PP} Transition		2		μs
t_{VPXA9X}	t_{AH9}	V_{PP} Transition to VA9 Transition		2		μs

Note: 1. V_{CC} must be applied simultaneously with or before V_{PP} and removed simultaneously or after V_{PP} .

Figure 6. MARGIN MODE AC Waveforms



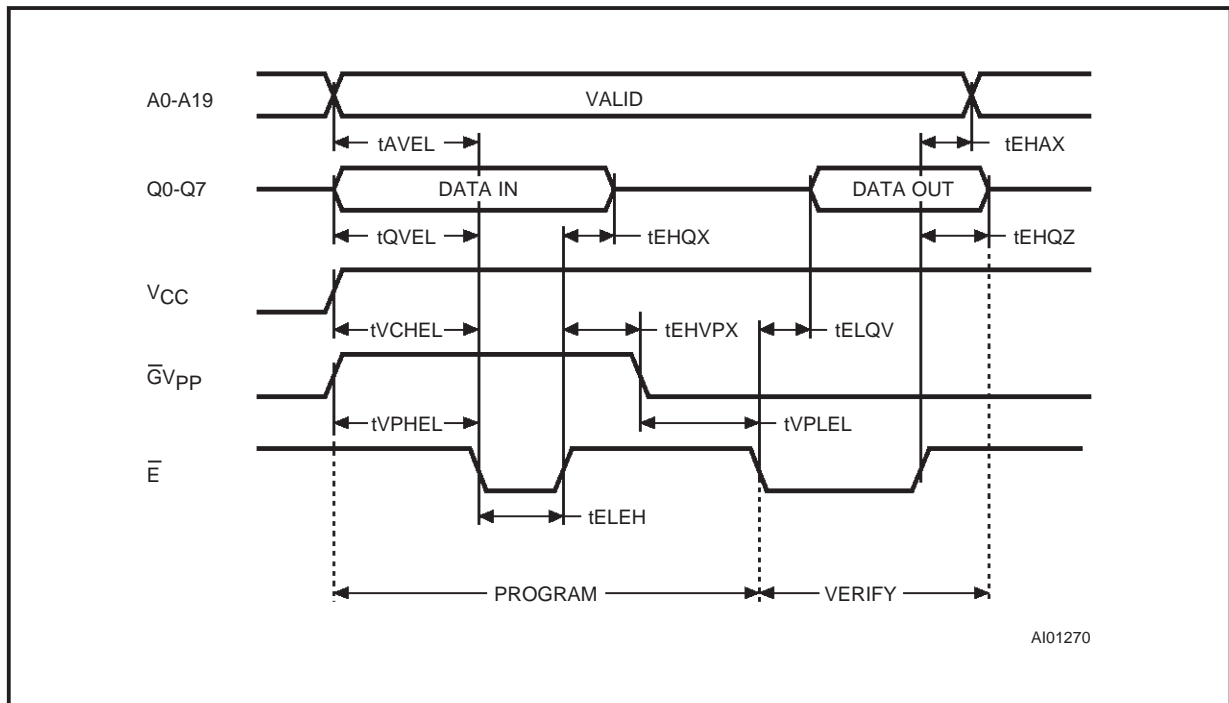
Note: A8 High level = 5V; A9 High level = 12V.

Table 11. Programming Mode AC Characteristics⁽¹⁾
 ($T_A = 25\text{ }^\circ\text{C}$; $V_{CC} = 6.25\text{V} \pm 0.25\text{V}$; $V_{PP} = 12.75\text{V} \pm 0.25\text{V}$)

Symbol	Alt	Parameter	Test Condition	Min	Max	Unit
t_{AVEL}	t_{AS}	Address Valid to Chip Enable Low		2		μs
t_{QVEL}	t_{DS}	Input Valid to Chip Enable Low		2		μs
t_{VCHEL}	t_{VCS}	V_{CC} High to Chip Enable Low		2		μs
t_{VPHEL}	t_{OES}	V_{PP} High to Chip Enable Low		2		μs
t_{VPLVPH}	t_{PRT}	V_{PP} Rise Time		50		ns
t_{ELEH}	t_{PW}	Chip Enable Program Pulse Width (Initial)		45	55	μs
t_{EHQX}	t_{DH}	Chip Enable High to Input Transition		2		μs
t_{EHVPX}	t_{OEH}	Chip Enable High to V_{PP} Transition		2		μs
t_{VPLEL}	t_{VR}	V_{PP} Low to Chip Enable Low		2		μs
t_{ELQV}	t_{DV}	Chip Enable Low to Output Valid			1	μs
t_{EHQZ} ⁽²⁾	t_{DFP}	Chip Enable High to Output Hi-Z		0	130	ns
t_{EHAX}	t_{AH}	Chip Enable High to Address Transition		0		ns

Notes: 1. V_{CC} must be applied simultaneously with or before V_{PP} and removed simultaneously or after V_{PP} .
 2. Sampled only, not 100% tested.

Figure 7. Programming and Verify Modes AC Waveforms



PRESTO IIB Programming Algorithm

PRESTO IIB Programming Algorithm allows the whole array to be programmed with a guaranteed margin, in a typical time of 52.5 seconds. This can be achieved with SGS-THOMSON M27W801 due to several design innovations to improve programming efficiency and to provide adequate margin for reliability. Before starting the programming the internal MARGIN MODE circuit is set in order to guarantee that each cell is programmed with enough margin. Then a sequence of 50 μ s program pulses are applied to each byte until a correct verify occurs. No overprogram pulses are applied since the verify in MARGIN MODE at V_{CC} much higher than 3.6V, provides the necessary margin.

Program Inhibit

Programming of multiple M27W801s in parallel with different data is also easily accomplished. Except for \bar{E} , all like inputs including \bar{G} and V_{PP} of the parallel M27W801 may be common. A TTL low level pulse applied to a M27W801's \bar{E} input, with V_{PP} at 12.75V, will program that M27W801. A high level \bar{E} input inhibits the other M27W801s from being programmed.

Program Verify

A verify (read) should be performed on the programmed bits to determine that they were correctly programmed. The verify is accomplished with \bar{G} at V_{IL} . Data should be verified with t_{ELQV} after the falling edge of \bar{E} .

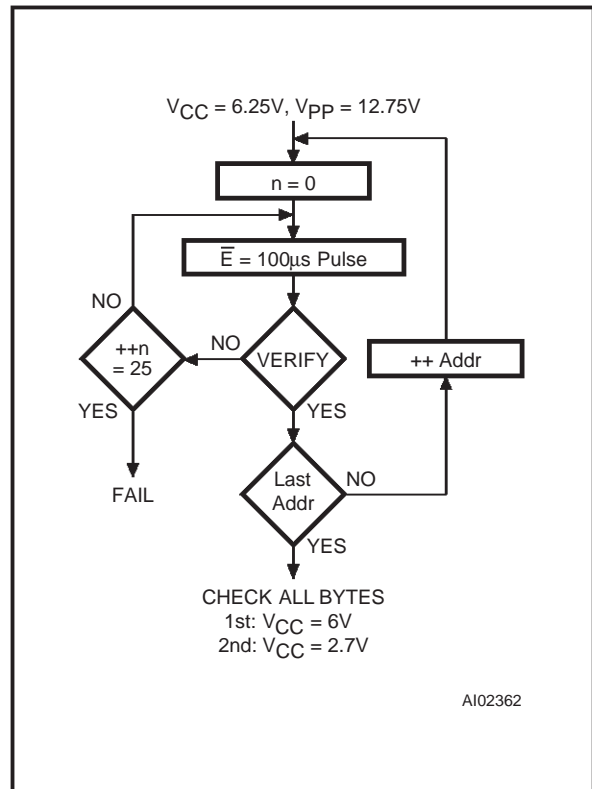
On-Board Programming

The M27W801 can be directly programmed in the application circuit. See the relevant Application Note AN620.

Electronic Signature

The Electronic Signature (ES) mode allows the reading out of a binary code from an EPROM that will identify its manufacturer and type. This mode is intended for use by programming equipment to automatically match the device to be programmed with its corresponding programming algorithm. The ES mode is functional in the 25°C \pm 5°C ambient temperature range that is required when program-

Figure 8. Programming Flowchart



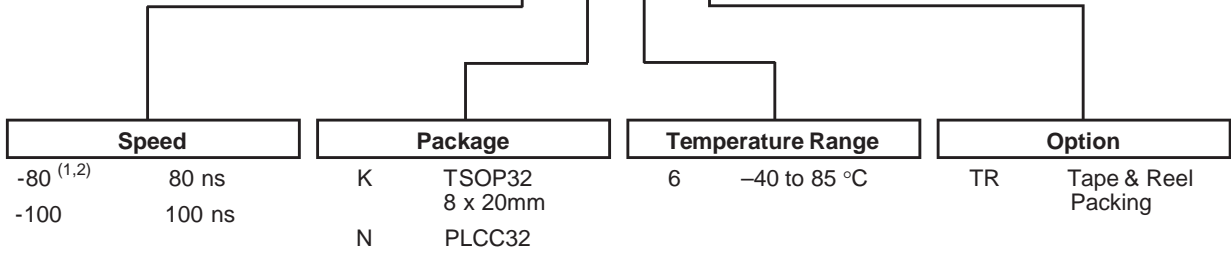
ming the M27W801. To activate the ES mode, the programming equipment must force 11.5V to 12.5V on address line A9 of the M27W801. Two identifier bytes may then be sequenced from the device outputs by toggling address line A0 from V_{IL} to V_{IH} . All other address lines must be held at V_{IL} during Electronic Signature mode.

Byte 0 ($A0=V_{IL}$) represents the manufacturer code and byte 1 ($A0=V_{IH}$) the device identifier code. For the SGS-THOMSON M27W801, these two identifier bytes are given in Table 4 and can be read-out on outputs Q0 to Q7.

Note that the M27W801 and M27C801 have the same identifier byte.

ORDERING INFORMATION SCHEME

Example: M27W801 -80 K 6 TR



NOT FOR NEW DESIGN ⁽³⁾	
-120	120 ns
-150	150 ns
-200	200 ns

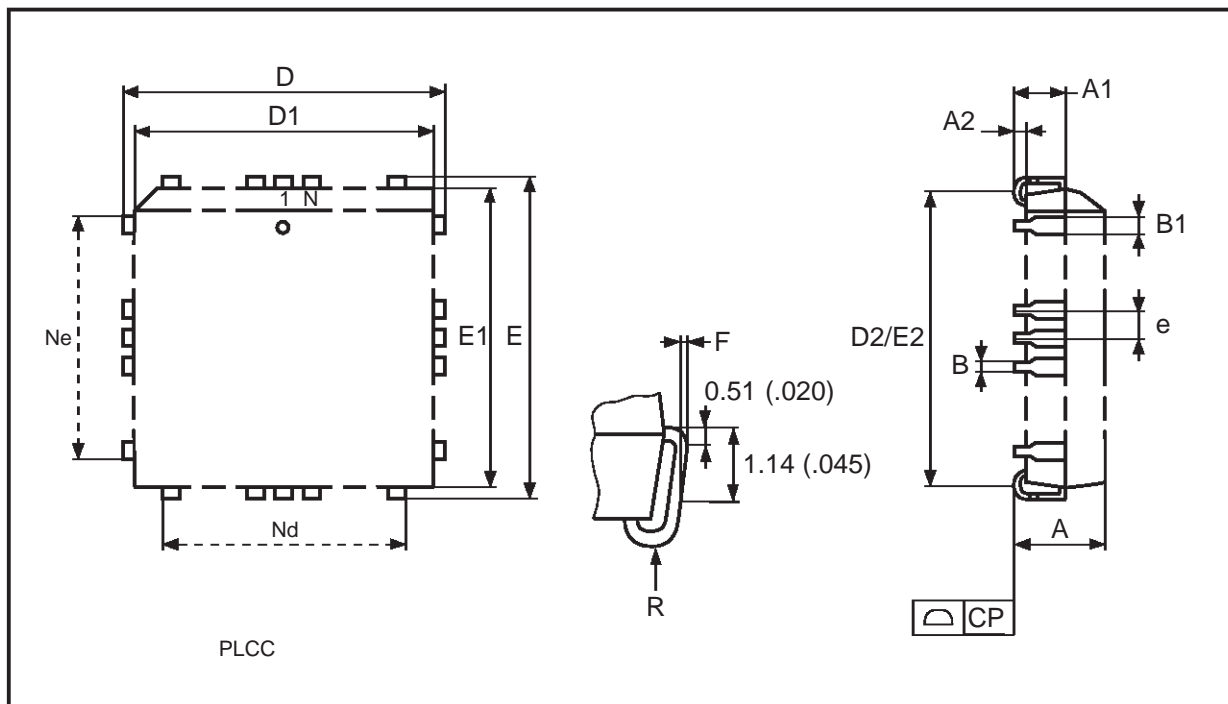
- Notes:**
1. High Speed, see AC Characteristics section for further information.
 2. This speed also guarantees 70ns access time at V_{CC} = 3.0V to 3.6V
 3. These speeds are replaced by the 100ns.

For a list of available options (Speed, Package, etc...) or for further information on any aspect of this device, please contact the SGS-THOMSON Sales Office nearest to you.



PLCC32 - 32 lead Plastic Leaded Chip Carrier, rectangular

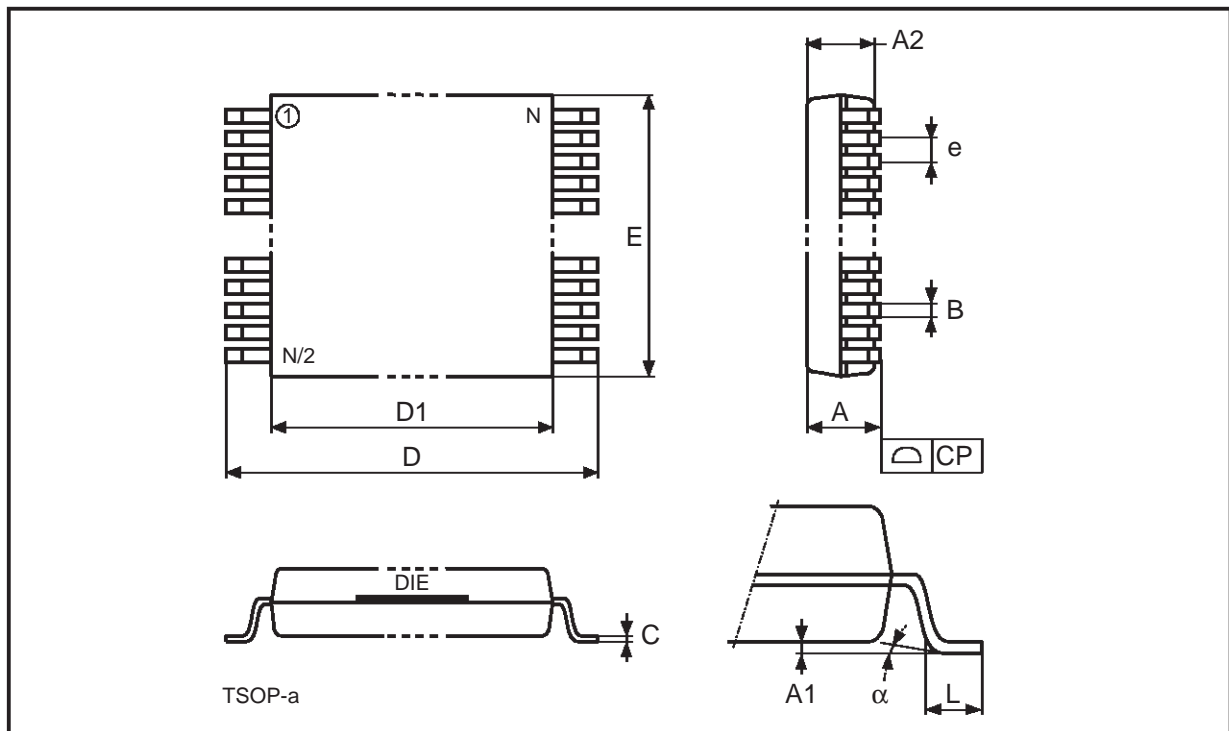
Symb	mm			inches		
	Typ	Min	Max	Typ	Min	Max
A		2.54	3.56		0.100	0.140
A1		1.52	2.41		0.060	0.095
A2		–	0.38		–	0.015
B		0.33	0.53		0.013	0.021
B1		0.66	0.81		0.026	0.032
D		12.32	12.57		0.485	0.495
D1		11.35	11.56		0.447	0.455
D2		9.91	10.92		0.390	0.430
E		14.86	15.11		0.585	0.595
E1		13.89	14.10		0.547	0.555
E2		12.45	13.46		0.490	0.530
e	1.27	–	–	0.050	–	–
F		0.00	0.25		0.000	0.010
R	0.89	–	–	0.035	–	–
N		32			32	
Nd		7			7	
Ne		9			9	
CP			0.10			0.004



Drawing is not to scale.

TSOP32 - 32 lead Plastic Thin Small Outline, 8 x 20mm

Symb	mm			inches		
	Typ	Min	Max	Typ	Min	Max
A			1.20			0.047
A1		0.05	0.17		0.002	0.006
A2		0.95	1.05		0.037	0.041
B		0.15	0.27		0.006	0.011
C		0.10	0.21		0.004	0.008
D		19.80	20.20		0.780	0.795
D1		18.30	18.50		0.720	0.728
E		7.90	8.10		0.311	0.319
e	0.50	–	–	0.020	–	–
L		0.50	0.70		0.020	0.028
α		0°	5°		0°	5°
N	32			32		
CP			0.10			0.004



Drawing is not to scale.

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